AMENDMENTS TO THE SPECIFICATION

Please amend paragraph 0006 as follows:

FIG. 13 shows an equivalent circuit when the high frequency transmission path 101 is ON (ON of Q101) and the shunt path 102 is OFF (OFF of Q102). The OFF capacitance Coff is sufficiently smaller than the capacitance of the DC cut capacitors C101 and C102 and an ON resistance Ron of FET Q101 is ~~about several~~on the order of several ohms (Ω). Therefore, the characteristics of the circuit of FIG. 13 are determined dominantly by a power leak in the transistor Q102, while the transistor is ~~by the~~ OFF and exhibiting a capacitance Coff. Conversely, while the high frequency transmission path is OFF and the shunt path 102 is ON, FET Q101 of the high frequency transmission path 101 ~~has the~~is OFF and exhibiting capacitance Coff~~, which~~ and leaks ~~a~~ power.

Please amend paragraph 0007 as follows:

As described above, if an RF signal is to be ~~shut~~ shunt by using only open/close of FET's, it becomes essentially difficult in a high frequency band particularly in view of the transmissive property of high-frequency signal. Namely, in the high frequency range, ~~a~~ when the transistor is ON then path loss ~~during ON~~ becomes large, and when the transistor is off then ~~a~~ sufficient isolation cannot be acquired ~~during OFF~~. ~~The~~ A ~~Similar~~ similar problem occurs even in the case of a circuit configuration using PIN (positive intrinsic negative) diodes, instead of ~~not~~ FETs. ~~but a PIN (positive intrinsic negative) diode.~~

Between paragraphs 0008 and 0009: change the phrase

~~DISCLOSURE~~ SUMMARY OF THE INVENTION

Please amend paragraph 00025 as follows:

As seen from FIG. 1, the high frequency circuit of the present embodiment is constituted of a plurality of, e.g., two shunt circuits 11 and 12 each having an active element and an impedance element or elements and implemented on the same substrate. The shunt circuit 11 is constituted of an active element 14 and an inductor L1 serially connected between a high frequency RF transmission path 13 and a ground. The other shunt circuit 12 is constituted of a capacitor C and an inductor L2 serially connected between the high frequency transmission path 13 and the ground, and an active element 15 connected in parallel to the inductor L2.

Please amend paragraph 00028 as follows:

As shown in FIG. 2, when the active elements 14 and 15 are ON (low resistance [=] is equivalent to Ron status), the high frequency circuit is in an ON status. In this status, the active elements 14 and 15 are considered equivalently an ON resistor Ron. This ON resistor Ron is sufficiently small in resistance and can be considered shorted. Therefore, the high frequency circuit in the ON status is equivalently a parallel resonance circuit of the inductor L1 and capacitor C, as shown in FIG. 3.

Please amend paragraph 0031 as follows:

On the other hand, as shown in FIG. 4, when the active elements 14 and 15 are OFF (high resistance [=] is equivalent to Coff status), the high frequency circuit is in an OFF status. In this status, an impedance Z1 of the shunt circuit 11 including the inductance L1 is:

Please amend paragraph 0044 as follows:

In the above-described embodiment, although the two shunt circuits 11 and 12 including the inductors L1 and L2 are used byway of example, the present invention is not limited thereto. As shown in FIG. 10, two shunt circuits including capacitors ~~C1 and C2~~C5 and C6 may be switched at the same time to obtain similar advantages described above. A circuit arrangement having three or more shunt paths may also be used.